



TO-92L Plastic-Encapsulate Transistors

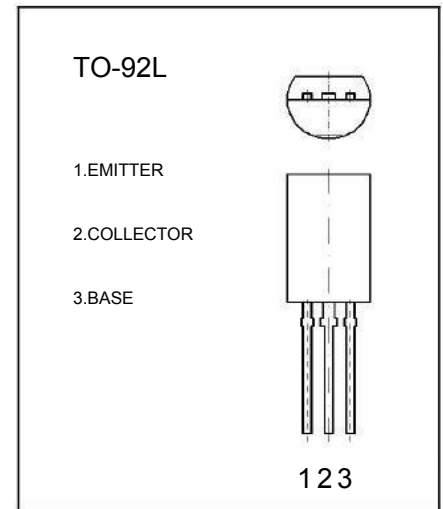
A1208 TRANSISTOR(PNP)

FEATURES

Low collector to emitter saturation voltage $V_{CE(sat)}$.
Complementary pair with C2910

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Units
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-0.07	A
P_C	Collector Power Dissipation	-0.9	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector cut-off current	I_{CBO}	$V_{CB}=-80V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-10\text{mA}$	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-30\text{mA}, I_B=-3\text{mA}$		-0.14	-0.4	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-10\text{mA}$		150		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	R	T
Range	100-200	140-280	200-400